



## Description

### JMT N-channel MOSFET

#### Features

- $V_{DS}=20V$ ,  $I_D=6A$
- $R_{DS(ON)}=13m\Omega$  (Typ.) @  $V_{GS}=4.5V$   
 $R_{DS(ON)}=17m\Omega$  (Typ.) @  $V_{GS}=2.5V$
- High Power and Current Handling Capability
- Lead Free Product is Acquired
- Surface Mount Package
- ESD Rating: HBM 3.5KV

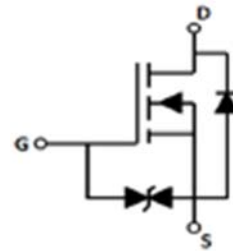
#### Application

- PWM Applications
- Load Switch
- Power Management

#### Package



SOT-23



### Absolute Maximum Ratings (T<sub>c</sub>=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units
V <sub>DSS</sub>	Drain-Source Voltage	20	V
V <sub>GSS</sub>	Gate-Source Voltage	±12	V
I <sub>D</sub>	Continuous Drain Current	T <sub>C</sub> = 25°C	6
		T <sub>C</sub> = 100°C	4
I <sub>DM</sub>	Pulsed Drain Current <sup>note1</sup>	24	A
P <sub>D</sub>	Power Dissipation	1.3	W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	96	°C/W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C



## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> = 250μA	20	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =20V, V <sub>GS</sub> = 0V,	-	-	1	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±10V	-	-	±10	μA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.4	0.62	1.0	V
R <sub>DSON</sub>	Static Drain-Source on-Resistance <small>note2</small>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	13	18	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A	-	17	22	
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz	-	980	-	pF
C <sub>oss</sub>	Output Capacitance		-	225	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	120	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =10V, I <sub>D</sub> =6A, V <sub>GS</sub> =4.5V	-	8	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	2	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	3	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5A, R <sub>L</sub> =1.5Ω, R <sub>GEN</sub> =3Ω	-	1.2	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	2.4	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	22	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	7	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	6	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	24	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> =6A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

## Typical Performance Characteristics

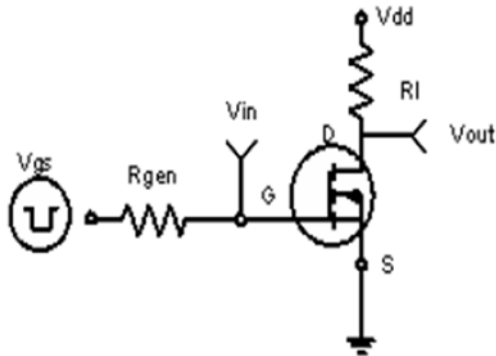


Figure1 :Switching Test Circuit

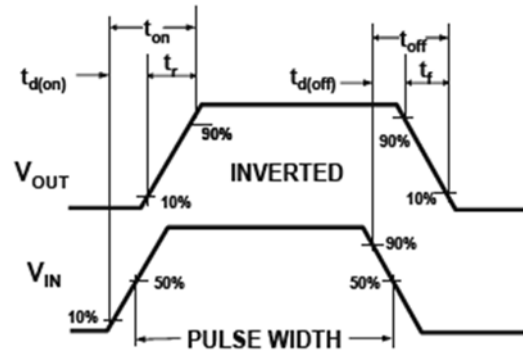
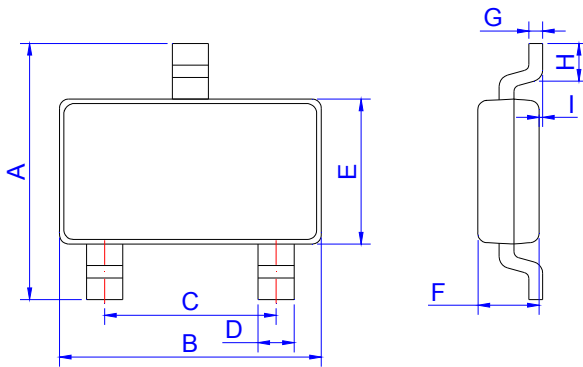


Figure2:Switching Waveforms

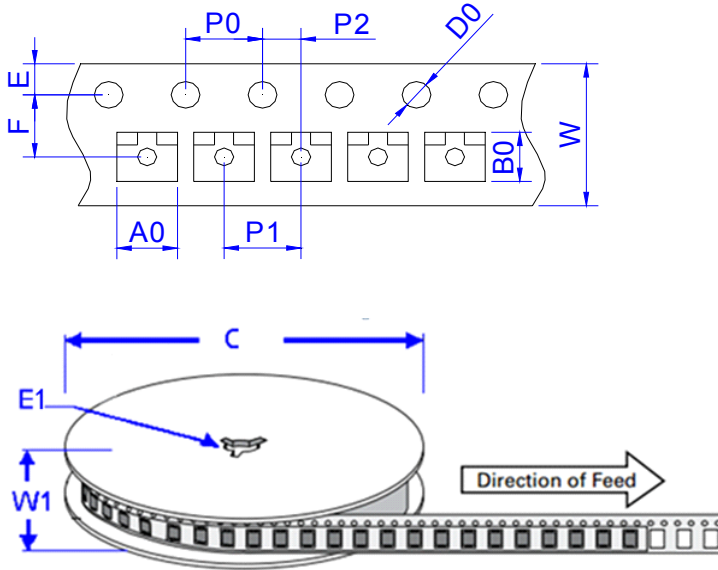
## Package Mechanical Data



SOT-23

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.30	2.40	2.50	0.091	0.095	0.098
B	2.80	2.90	3.00	0.110	0.114	0.118
C	1.90 REF			0.075 REF		
D	0.35	0.40	0.45	0.014	0.016	0.018
E	1.20	1.30	1.40	0.047	0.051	0.055
F	0.90	1.00	1.10	0.035	0.039	0.043
G		0.10	0.15		0.004	0.006
H	0.20			0.008		
I	0		0.10	0		0.004

## Package Information-SOT-23



Ref.	Dimensions	
	Millimeters	Inches
A0	3.15 ± 0.3	0.124 ± 0.012
B0	2.77 ± 0.3	0.109 ± 0.012
C	178	7.0
D0	1.50±0.1	0.059 ± 0.004
E	1.75 ± 0.2	0.069 ± 0.008
E1	13.3±0.3	0.524± 0.012
F	3.5 ± 0.2	0.138 ± 0.008
P0	4.00 ± 0.2	0.157 ± 0.008
P1	4.00 ± 0.2	0.157 ± 0.008
P2	2.00 ± 0.2	0.079 ± 0.008
W	8.00 ± 0.2	0.315 ± 0.008
W1	11.5±1.0	0.453 ± 0.039

## Ordering Information-SOT-23

OUTLINE	PACKAGE TYPE	QUANTITY REEL	DESCRIPTION
TAPING	SOT-23	3,000pcs	7 inch reel pack

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